PNP 5 GHz wideband transistor Rev. 3 — 22 January 2016

Product data sheet

1. Product profile

1.1 General description

PNP transistor in a plastic SOT23 envelope. It is primarily intended for use in RF wideband amplifiers, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analyzers, etc. The transistor features low intermodulation distortion and high power gain; due to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies. NPN complements are BFR92 and BFR92A.

1.2 Features and benefits

- High power gain
- Low intermodulation distortion

1.3 Applications

- Oscilloscopes and spectrum analyzers
- Radar systems
- RF wideband amplifiers

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-	-20	V
V_{CEO}	collector-emitter voltage	open base	-	-	-15	V
I _C	DC collector current		-	-	-25	mA
P _{tot}	total power dissipation	up to $T_s = 95 ^{\circ}C$	-	-	300	mW
f _T	transition frequency	$I_C = -14 \text{ mA}$; $V_{CE} = -10 \text{ V}$; $f = 500 \text{ MHz}$	-	5	-	GHz
C _{re}	feedback capacitance	$I_C = -2 \text{ mA}; V_{CE} = -10 \text{ V}; f = 1 \text{ MHz}$	-	0.7	-	pF
G _{UM}	maximum unilateral power gain	$I_C = -14 \text{ mA}; V_{CE} = -10 \text{ V}; f = 500 \text{ MHz}$ $T_{amb} = 25 \text{ °C};$	-	18	-	dB
NF	noise figure	$I_C = -5 \text{ mA}$; $V_{CE} = -10 \text{ V}$; $f = 500 \text{ MHz}$; $T_{amb} = 25 \text{ °C}$	-	2.5	-	dB
d _{im}	intermodulation distortion	$I_{C} = -14$ mA; $V_{CE} = -10$ V; $R_{L} = 75 \Omega$; $V_{o} = 150$ mV; $T_{amb} = 25$ °C; $f_{(p+q-r)} = 493.25$ MHz	-	-60	-	dB

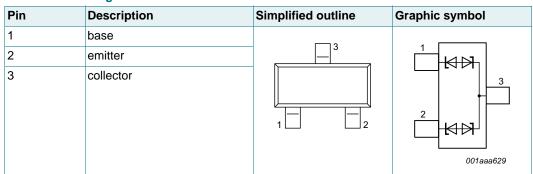
^[1] T_s is the temperature at the soldering point of the collector tab.



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2. Pinning information

Table 2. Pinning



3. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BFT92	TO-236AB	Plastic surface mounted package; 3 leads	SOT23			

4. Marking

Table 4. Marking codes

Type number	Marking code
BFT92	W1%

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-20	V
V_{CEO}	collector-emitter voltage	open base		-	-15	V
V_{EBO}	emitter-base voltage	open collector		-	-2	V
I _C	DC collector current			-	-25	mA
I _{CM}	peak collector current	f > 1 MHz		-	-35	mA
P _{tot}	total power dissipation	up to T _s = 95 °C	<u>[1]</u>	-	300	mW
T _{stg}	storage temperature			-65	150	°C
Tj	junction temperature			-	175	°C

^[1] T_s is the temperature at the soldering point of the collector tab.

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th j-s}	thermal resistance from junction to soldering point	up to $T_s = 95 ^{\circ}C$	260	K/W

^[1] T_s is the temperature at the soldering point of the collector tab.

7. Characteristics

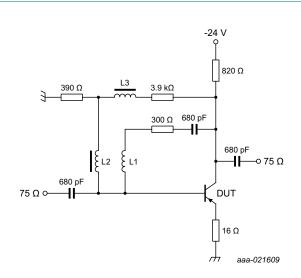
Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -10 \text{ V}$	-	-	-50	nΑ
h _{FE}	DC current gain	$I_C = -14 \text{ mA}; V_{CE} = -10 \text{ V}$	20	50	-	
f _T	transition frequency	$I_C = -14 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 500 MHz	-	5	-	GHz
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	-	0.75	-	pF
C _e	emitter capacitance	$I_C = I_c = 0$; $V_{EB} = -0.5 \text{ V}$; $f = 1 \text{ MHz}$	-	8.0	-	pF
C _{re}	feedback capacitance	$I_C = -2 \text{ mA}$; $V_{CE} = -10 \text{ V}$; $f = 1 \text{ MHz}$	-	0.7	-	pF
G _{UM}	maximum unilateral power gain	$I_C = -14 \text{ mA}; V_{CE} = -10 \text{ V};$ $f = 500 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	18	-	dB
NF	noise figure	$I_C = -5 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 500 MHz; $T_{amb} = 25 \text{ °C}$	-	2.5	-	dB
V _o	output voltage	$\begin{array}{l} d_{im} = -60 \text{ dB (DIN } 45004\text{B); } I_{C} = -14 \text{ mA;} \\ V_{CE} = -10 \text{ V; } R_{L} = 75 \Omega; \\ V_{p} = V_{o} \text{ at } d_{im} = -60 \text{ dB; } f_{p} = 495.25 \text{ MHz;} \\ V_{q} = V_{o} -6 \text{ dB; } f_{q} = 503.25 \text{ MHz;} \\ V_{r} = V_{o} -6 \text{ dB; } f_{r} = 505.25 \text{ MHz;} \\ \text{measured at } f_{(p+q-r)} = 493.25 \text{ MHz.} \end{array}$	-	150	-	mV

[1]
$$G_{UM}$$
 is the maximum unilateral power gain, assuming S12 is zero and $G_{UM} = 10 \log \frac{\left|S_{2I}\right|^2}{(I - \left|S_{II}\right|^2)(I - \left|S_{22}\right|^2)} dB$

8. Graphs



L2 = L3 = 5 uH Ferroxcube choke, catalogue number 3122 108 20150

L1 = 4 turns 0.35 mm copper wire; winding pitch 1 mm; internal diameter 4 mm

Fig 1. Intermodulation distortion test circuit

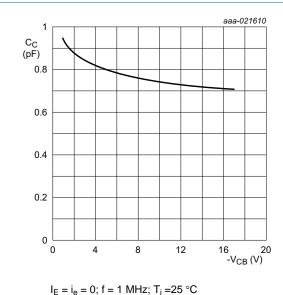


Fig 3. Collector capacitance as a function of collector-base voltage

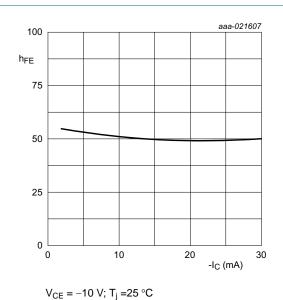
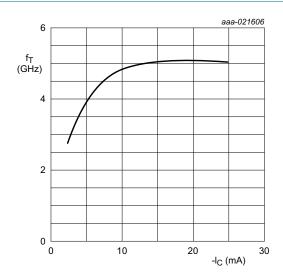


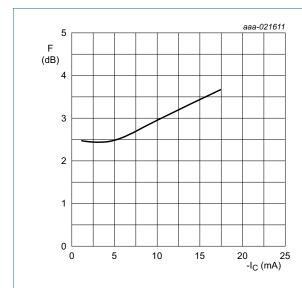
Fig 2. DC current gain as a function of collector current



 $V_{CE} = -10 \text{ V; } f = 500 \text{ MHz; } T_j = 25 \text{ }^{\circ}\text{C}$

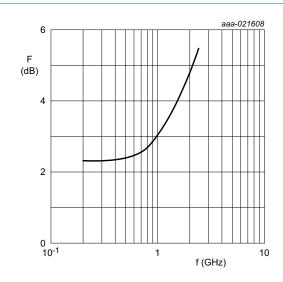
Fig 4. Transistion frequency as a function of collector current

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 $V_{CE} = -10 \text{ V}; Z_s = \text{opt}; f = 500 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 5. Minimum noise figure as a function of collector current.



 I_C = -2 mA; V_{CE} = -10 V; Z_s = opt; T_{amb} = 25 °C

Fig 6. Minimum noise figure as a function of frequency.

9. Package outline

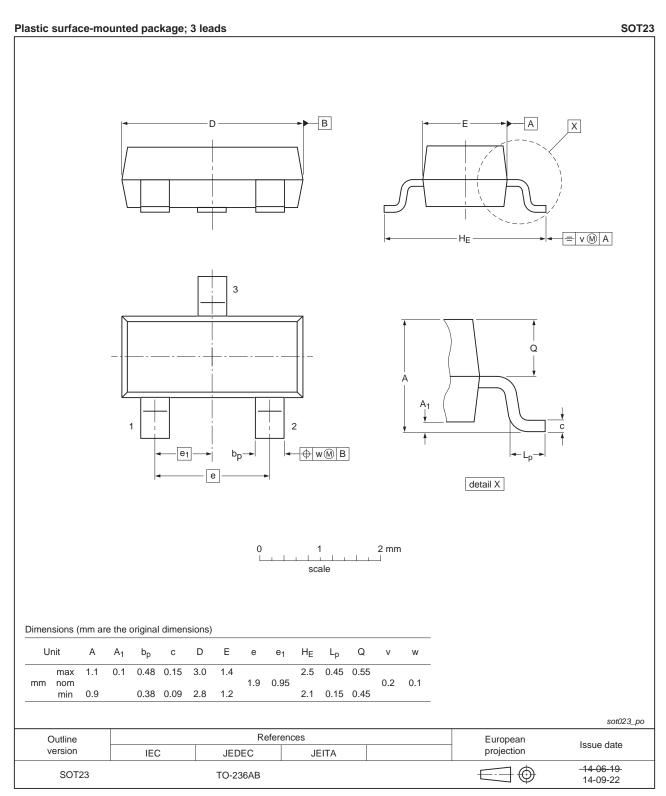


Fig 7. Package outline SOT23 (TO-236AB)

10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BFT92 v.3	20160122	Product data sheet	-	BFT92 v.2		
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	 Legal texts have been adapted to the new company name where appropriate. 					
BFT92 v.2	19921101	Product specification	-	-		

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11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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